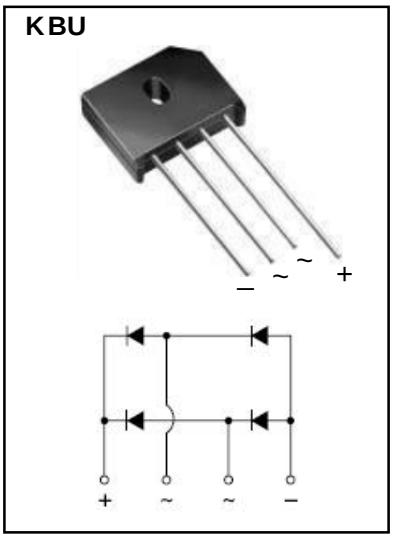
SZCJ

Shenzhen Changji Semiconductor Co., LTD.

Features

- I_O 8A
- VRRM 50V-1000V
- High surge current capability
- Glass passivated chip



Applications

- General purpose 1 phase Bridge rectifier applications

Marking

- KBU8XX

XX：From 005 To 10

Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	KBU8						
				005	01	02	04	06	08	10
Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
Average Rectified Output Current	I_O	A	60Hz sine wave, R-load ,T_c =100℃	8						
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60H_Z half-sine wave, 1 cycle, T_j=25℃	200						
Current Squared Time	I^2t	A^2S	1ms≤t<8.3ms Tj=25℃， Rating of per diode	166						
Storage Temperature	T_{stg}	℃		-55 ~+150						
Junction Temperature	T_j	℃		-55 ~+150						

Electrical Characteristics（T_a=25℃ Unless otherwise specified）

Item	Symbol	Unit	Test Condition	Max
Peak Forward Voltage	V_{FM}	V	I_{FM}=4.0A, Pulse measurement, Rating of per diode	1.0
Peak Reverse Current	I_{RRM}	μA	V_{RM}=V_{RRM} , Pulse measurement, Rating of per diode	10
Thermal Resistance	$R_{\theta J-A}$	℃/W	Between junction and ambient	9
	$R_{\theta J-C}$		Between junction and case	3.7

Typical Characteristics

FIG.1-MAXIMUM FORWARD SURGE CURRENT

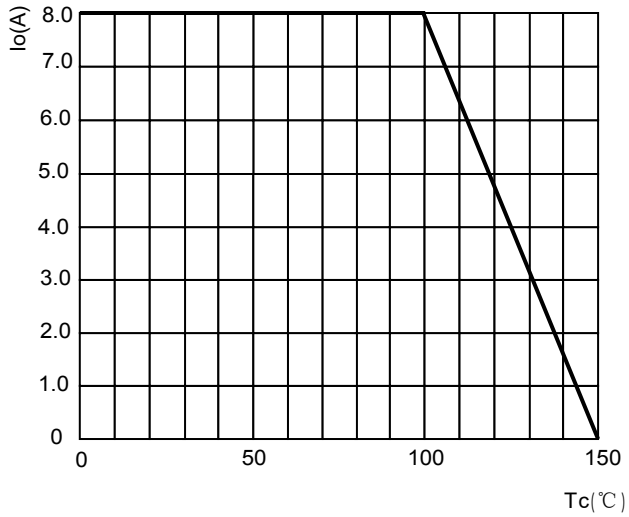


FIG.2-TYPICAL FORWARD CHARACTERISTICS

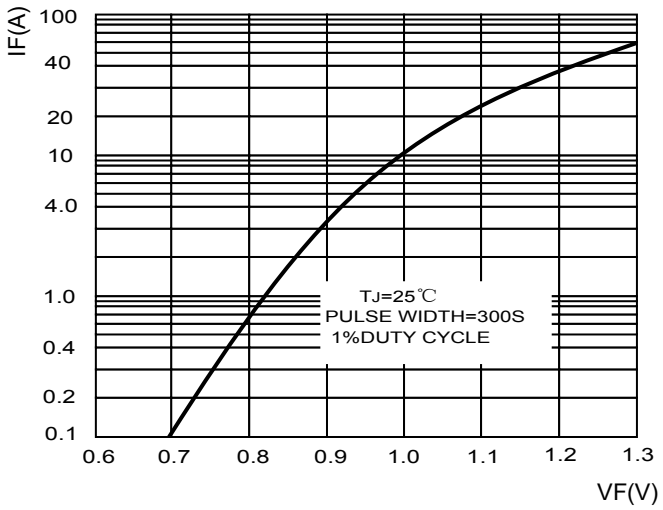


FIG.3-MAXIMUM NON-REPETITIVE SUNRGE CURRENT

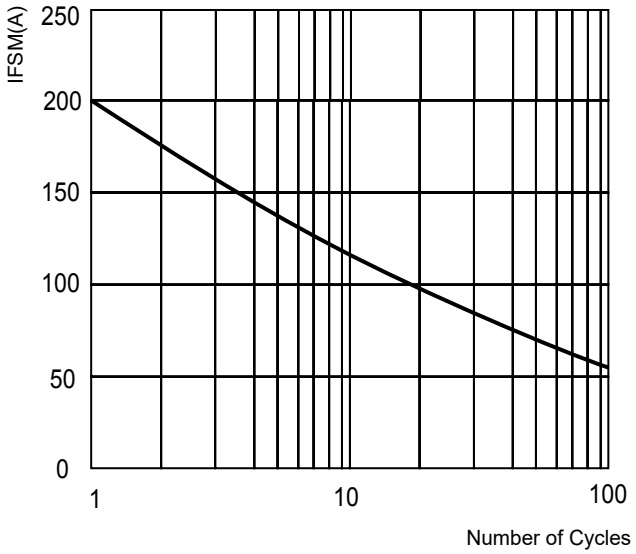


FIG.4-TYPICAL REVERSE CHARACTERISTICS

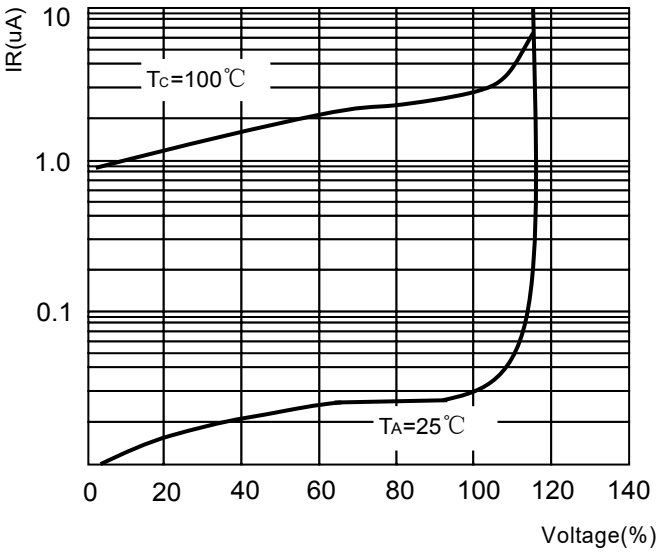
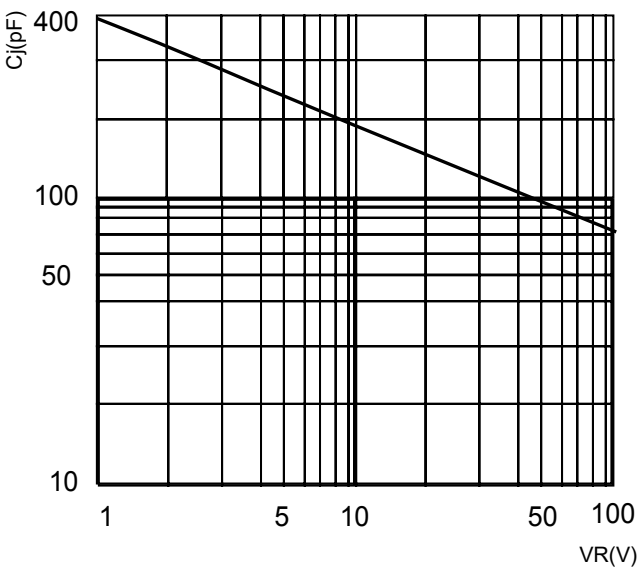
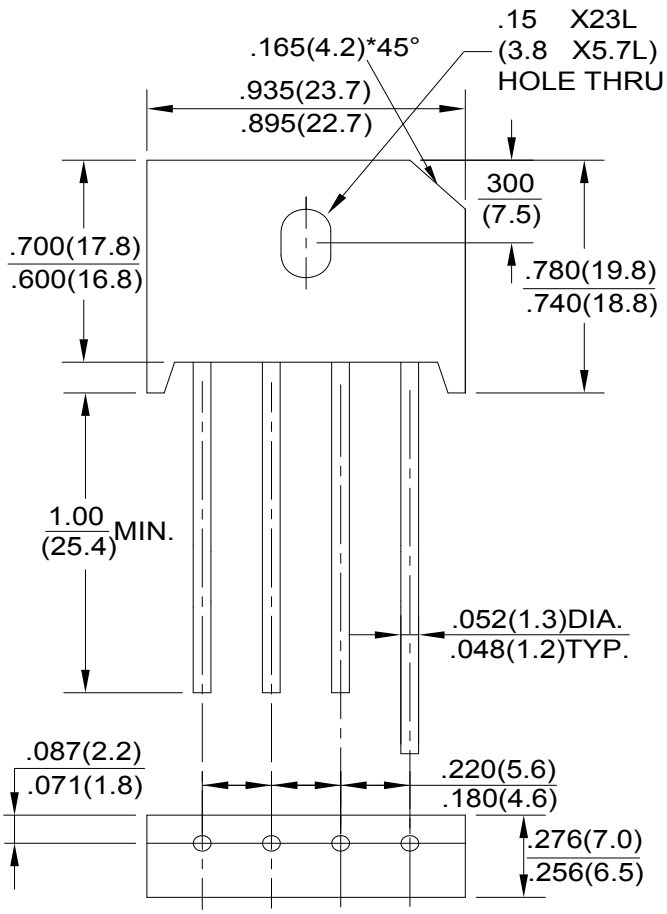


FIG.5-TYPICAL JUNCTION CAPACITANCE



KBU Package Outline Dimensions



Dimensions in inches and (milimeters)

NOTICE

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